

SOLID STATE ABSTRACTS

*A reference journal devoted to the
theory, production and use of solid state materials and devices*

VOLUME 5

ANNUAL CUMULATIVE INDEX ISSUE

**PHYSICS
METALLURGY
ELECTRONICS**

**SEMICONDUCTORS
PHOSPHORS
MAGNETICS
DIELECTRICS
SUPERCONDUCTORS
METALS**

SOLID STATE ABSTRACTS

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PREFACE

The increasing numbers of solid state oriented articles, texts, conferences and reports and the subsequent increase in abstracts on this literature have necessitated the printing of the Annual Cumulative Index in this separate issue.

This increase has expanded the Subject Index to a point where a breakdown between topic and material is considered advisable. The Subject Index is therefore divided into: (I) Topic Index - entries relating to properties and shapes of materials, devices, circuits and device applications; and (II) Material Index - entries relating to specific elements, compounds and classes of materials (dielectrics, semiconductors, etc.).

The Editor

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